CNC7S101, CNZ3182, CNC7T101, CNC1H101 (ON3181, ON3182, ON3183, ON3184)

Optoisolators

Overview

CNC7S101 is an AC input compatible optoisolator in which two GaAs high output infrared light emitting diode chips are connected in reverse parallel as light emitting elements, and opitically are connected to a high sensitivity Si phototransistor chip as a light detecting element in a small DIL 4-pin package.

This optoisolator series also includes the two-channel CNZ3182, the three-channel CNC7T101, and the four-channel CNC1H101.

The CNC7S101 series has a number of excellent features, including high I/O isolation voltage and current transfer ratio (CTR), as well as high speed response and high reliability.

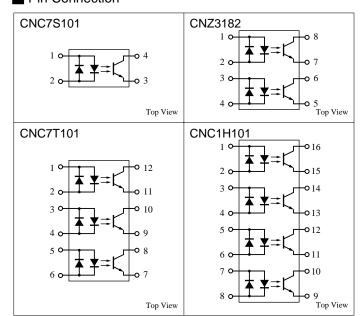
Features

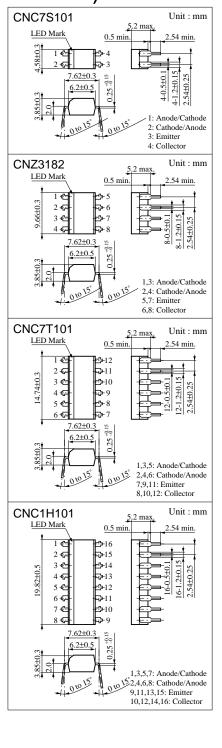
- www.DataShe of All support
 - High I/O isolation voltage : $V_{ISO} = 5000 V_{rms}$ (min.)
 - Fast response : $t_r = 4 \mu s$, $t_f = 3 \mu s$
 - UL listed (UL File No. E79920)

Applications

- Telephones
- Telephone switches
- Programmable controllers
- AC/DC input modules for measuring

■ Pin Connection





Note) The part numbers in the parenthesis show conventional part number.

■ Absolute Maximum Ratings (Ta = 25°C)

F	Parameter	Symbol	Ratings	Unit
I d'il	Forward current (DC)	I_F	±50	mA
Input (Light emitting diode)	Pulse forward current	I_{FP}^{*1}	±1	A
	Power dissipation	P _D *2	75	mW
Output (Photo transistor)	Collector current	I_{C}	50	mA
	Collector to emitter voltage	V_{CEO}	80	V
	Emitter to collector voltage	V _{ECO}	7	V
	Collector power dissipation	P _C *3	150	mW
Total power di	P_{T}	200	mW	
Isolation volta	V _{ISO} *4	5000	V_{rms}	
Operating amb	T _{opr}	-30 to +100	°C	
Storage tempe	T _{stg}	-55 to +125	°C	

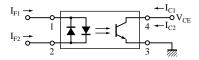
^{*1} Pulse width ≤ 100 µs, repeat 100 pps

■ Electrical Characteristics (Ta = 25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Input characteristics	Forward voltage (DC)	V _F	$I_F = \pm 50 \text{mA}$		1.35	1.5	V
	Capacitance between pins	C _t	$V_R = 0V, f = 1MHz$		35		pF
Output characteristics	Collector cutoff current	I _{CEO}	$V_{CE} = 20V$		5	100	nA
	Collector to emitter voltage	V _{CEO}	$I_C = 100\mu A$	80			V
	Emitter to collector voltage	V _{ECO}	$I_E = 10\mu A$	7			V
	Collector to emitter capacitance	C _C	$V_{CE} = 10V, f = 1MHz$		3		pF
Transfer characteristics	DC current transfer ratio	CTR*1, 5	$V_{CE} = 5V$, $I_F = \pm 1 \text{mA}$	20		300	%
	Isolation capacitance, input to output	C _{ISO}	f = 1MHz		0.6		pF
	Isolation resistance, input to output	R _{ISO}	$V_{\rm ISO} = 500 \text{V}$	1011			Ω
	Rise time	t _r *2	$V_{CC} = 10V, I_C = 2mA,$		4		μs
	Fall time	t _f *3	$R_{\rm L} = 100\Omega$		3		μs
	Collector to emitter saturation voltage	V _{CE(sat)}	$I_F = \pm 20 \text{mA}, I_C = 1 \text{mA}$		0.1	0.2	V
	Collector current ratio	I _{C(Ratio)} *4	$V_{CE} = 5V, I_F = 1mA$	0.33	1.0	3.0	_

^{*1} DC current transfer ratio (CTR) is a ratio of output current against DC input current

*4
$$I_{C \text{ (Ratio)}} = \frac{I_{C2} (I_F = I_{F2}, V_{CE} = 5V)}{I_{C1} (I_F = I_{F1}, V_{CE} = 5V)}$$



*5 CTR classifications

Class	General	R	S
CTR (%)	20 to 300	50 to 150	100 to 300

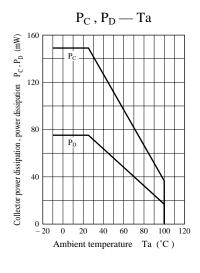
^{*2} Input power derating ratio is $0.75 \text{ mW/}^{\circ}\text{C}$ at $\text{Ta} \ge 25 ^{\circ}\text{C}$.

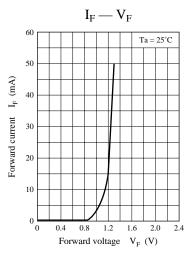
^{*3} Output power derating ratio is 1.5 mW/°C at Ta \geq 25°C.

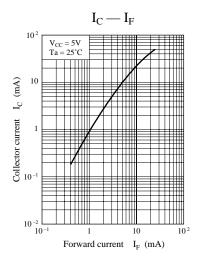
^{*4} AC 1 min. RH < 60 %

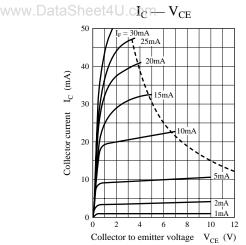
 $^{^{*2}}$ t_{r} : Time required for the collector current to increase from 10% to 90% of its final value

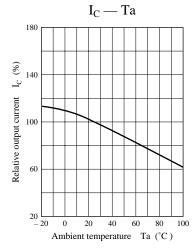
 $^{^{*3}}$ $t_{\rm f}$: Time required for the collector current to decrease from 90% to 10% of its initial value

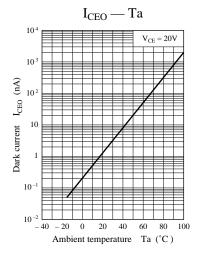


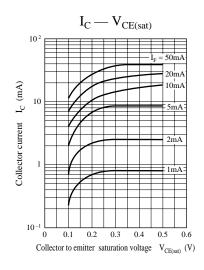


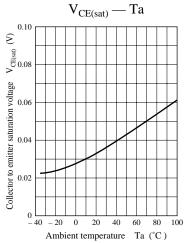


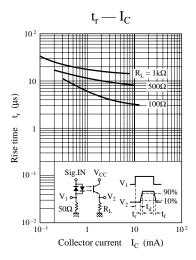


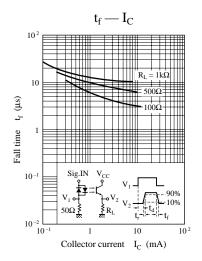


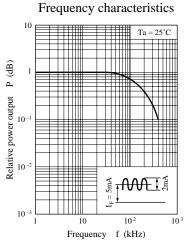




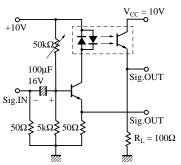








Measuring circuit of frequency characteristics



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